

DUAL ULTRAFAST POWER RECTIFIER

Qualified per MIL-PRF-19500/645

DEVICES

1N6772 **1N6772R**
1N6773 **1N6773R**

LEVELS

JAN
JANTX
JANTXV

ABSOLUTE MAXIMUM RATINGS ($T_C = +25^\circ\text{C}$ unless otherwise noted) (Per Diode)

Parameters / Test Conditions	Symbol	Value	Unit
Peak Repetitive Reverse Voltage $I_D = 5\mu\text{A}$ dc	V_{RWM}	400 600	Vdc
Average Forward Current ⁽¹⁾ $T_C = +100^\circ\text{C}$	I_F	8	A dc
Peak Surge Forward Current	I_{FSM}	60	A(pk)
Thermal Resistance - Junction to Case	$R_{\theta jc}$	2.5	$^\circ\text{C/W}$

Note:

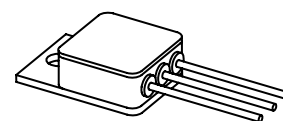
(1) Derate linearly @ 160mA/ $^\circ\text{C}$ above $T_C = 100^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise noted)

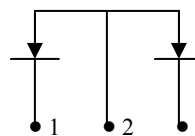
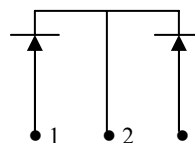
Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Breakdown Voltage ⁽²⁾ 1N6772, R 1N6773, R	V_{BR}	400 600		Vdc
Forward Voltage $I_F = 4\text{A}$ dc ⁽²⁾ $I_F = 8\text{A}$ dc ⁽²⁾	V_{F1} V_{F2}		1.45 1.60	Vdc
Reverse Leakage Current $V_R = 320\text{V}$ ⁽²⁾ $V_R = 480\text{V}$ ⁽²⁾ 1N6772, R 1N6773, R	I_{R1}		10	μA dc
Reverse Leakage Current $V_R = 320\text{V}$ ⁽²⁾ , $T_C = +100^\circ\text{C}$ $V_R = 480\text{V}$ ⁽²⁾ , $T_C = +100^\circ\text{C}$ 1N6772, R 1N6773, R	I_{R2}		500	μA dc
Reverse Recovery Time $I_F = 1\text{A}$, $di/dt = 50\text{A}/\mu\text{s}$	t_{rr}		60	nS
Junction Capacitance $V_R = 5\text{V}$ dc, $f = 1.0\text{MHz}$	C_J		200	pF

Note:

(2) Pulse Test; 300 μs , duty cycle $\leq 2\%$



TO-257



Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[Microchip:](#)

[JAN1N6772R](#) [JAN1N6773R](#) [JAN1N6772](#)